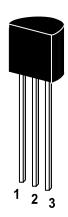
PNP Silicon Epitaxial Planar Transistor

For high voltage applications.

The transistor is subdivided into two groups, G and L according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	120	V
Collector Emitter Voltage	-V _{CEO}	120	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	100	mA
Emitter Current	I _E	100	mA
Power Dissipation	P _{tot}	300	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	-55 to +125	°C







ST 2SA1268

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V _{CE} =6V, -I _C =2mA					
Current Gain Group G	h _{FE}	200	-	400	-
L	h _{FE}	350	-	700	-
Collector Emitter Breakdown Voltage					
at -I _C =1mA	-V _{(BR)CEO}	120	-	-	V
Gain Bandwidth Product					
at -V _{CE} =6V, -I _C =1mA	f _T	-	100	-	MHz
Noise Figure					
at -V _{CE} =6V, -I _C =0.1mA, R _G =10k Ω , f=10Hz	NF	-	-	6	dB
Output Capacitance					
at -V _{CB} =10V, f=1MHz	C _{OB}	-	4	-	pF
Base Emitter Voltage					
at -V _{CE} =6V,-I _C =2mA	-V _{BE}	-	0.65	-	V
Collector Cutoff Current					
at -V _{CB} =120V	-I _{CBO}	-	-	0.1	μΑ
Emitter Cutoff Current					
at -V _{EB} =5V	-I _{EBO}	-	-	0.1	μΑ
Collector Saturation Voltage					
at -I _C =10mA, -I _B =1mA	-V _{CE(sat)}	-	-	0.3	V







